

Fahrettin Sarcan

List of Publications by Year in descending order

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24
papers

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933447

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24
times ranked

142
citing authors

#	ARTICLE	IF	CITATIONS
1	Bismuth-induced effects on optical, lattice vibrational, and structural properties of bulk GaAsBi alloys. <i>Nanoscale Research Letters</i> , 2014, 9, 119.	5.7	33
2	Magnetotransport study on as-grown and annealed n- and p-type modulation-doped GaInNAs/GaAs strained quantum well structures. <i>Nanoscale Research Letters</i> , 2014, 9, 141.	5.7	16
3	Influence of nitrogen on hole effective mass and hole mobility in p-type modulation doped GaInNAs/GaAs quantum well structures. <i>Applied Physics Letters</i> , 2013, 103, 082121.	3.3	15
4	Dilute nitride resonant-cavity light emitting diode. <i>Optics and Laser Technology</i> , 2020, 122, 105888.	4.6	15
5	An analysis of Hall mobility in as-grown and annealed n- and p-type modulation-doped GaInNAs/GaAs quantum wells. <i>Nanoscale Research Letters</i> , 2012, 7, 529.	5.7	14
6	Dilute nitride resonant cavity enhanced photodetector with internal gain for the $\lambda = 1.3 \mu\text{m}$ optical communications window. <i>Superlattices and Microstructures</i> , 2015, 86, 467-471.	3.1	14
7	Analytic modeling of temperature dependence of 2D carrier mobility in as-grown and annealed GaInNAs/GaAs quantum well structures. <i>Semiconductor Science and Technology</i> , 2014, 29, 125009.	2.0	13
8	ZnO nanoparticles-based vacuum pressure sensor. <i>Nanotechnology</i> , 2020, 31, 435502.	2.6	13
9	Excitation energy-dependent nature of Raman scattering spectrum in GaInNAs/GaAs quantum well structures. <i>Nanoscale Research Letters</i> , 2012, 7, 656.	5.7	12
10	Characterization of temperature dependent operation of a GaInNAs-based RCEPD designed for $1.3 \mu\text{m}$. <i>Superlattices and Microstructures</i> , 2017, 102, 27-34.	3.1	12
11	Quantum oscillations and interference effects in strained n- and p-type modulation doped GaInNAs/GaAs quantum wells. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 305108.	2.8	10
12	A study on the voltage-dependent response of a GaInNAs-based <i>pin</i> photodetector with a quasi-cavity. <i>Semiconductor Science and Technology</i> , 2018, 33, 114006.	2.0	10
13	Ultraviolet Photodetector Based on $\text{Mg}_{0.67}\text{Ni}_{0.33}\text{O}$ Thin Film on SrTiO_3 . <i>Physica Status Solidi - Rapid Research Letters</i> , 2020, 14, 2000175.	2.4	8
14	A study of electric transport in n- and p-type modulation-doped GaInNAs/GaAs quantum well structures under a high electric field. <i>Semiconductor Science and Technology</i> , 2018, 33, 064003.	2.0	6
15	Effects of annealing temperature on a ZnO thin film-based ultraviolet photodetector. <i>Physica Scripta</i> , 2022, 97, 015803.	2.5	6
16	In vitro comparison of titanium surface conditioning via boron-compounds and sand-blasting acid-etching. <i>Surfaces and Interfaces</i> , 2020, 21, 100703.	3.0	5
17	Negative and positive magnetoresistance in GaInNAs/GaAs modulation-doped quantum well structures. <i>Applied Physics A: Materials Science and Processing</i> , 2015, 118, 823-829.	2.3	4
18	Temporal Response of Dilute Nitride Multi-Quantum-Well Vertical Cavity Enhanced Photodetector. <i>Journal of Electronic Materials</i> , 2018, 47, 655-661.	2.2	3

#	ARTICLE	IF	CITATIONS
19	Determination of the acoustic phonon-hot carriers interaction in n- and p-type modulation-doped GaInNAs/GaAs quantum wells. <i>Physica B: Condensed Matter</i> , 2021, 612, 412946.	2.7	3
20	Temperature-dependent sandwich and in-plane optical characterization of ternary chalcogenide TlSbS ₂ . <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2021, 272, 115322.	3.5	3
21	Surface acoustic wave quasi-Bessel beams generated by symmetrically tilted interdigital transducers. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 225303.	2.8	3
22	Photoluminescence characteristic of as-grown and thermally annealed n- and p-type modulation-doped Ga _{0.68} In _{0.32} N _x As _{1-x} /GaAs quantum well structures. <i>Thin Solid Films</i> , 2021, 732, 138785.	1.8	1
23	Effect of thermal annealing and nitrogen composition on quantum transport in GaInNAs alloy based modulation doped quantum well structures. <i>Journal of Alloys and Compounds</i> , 2017, 695, 404-409.	5.5	0
24	Nitrogen induced localised-state ensemble effect on multi quantum well GaInNAs with low indium concentration. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 245105.	2.8	0